

N-Channel Power MOSFET

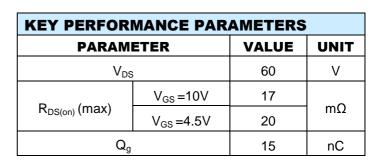
 $60V, 42A, 17m\Omega$

FEATURES

- 100% avalanche tested
- Suitable for 5V drive applications
- Pb-free plating
- RoHS compliant
- Halogen-free mold compound

APPLICATION

- SMPS Synchronous Rectification
- Networking DC-DC Power System





TO-251 (IPAK)

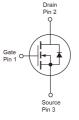




TO-251S (IPAK SL)



TO-252 (DPAK)



Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current (Note 1)	$T_{\rm C} = 25^{\circ}{\rm C}$	- I _D	38	•	
	$T_{c} = 100^{\circ}C$		24	A	
Pulsed Drain Current (Note 2)		I _{DM}	152	А	
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	20	mJ	
Single Pulsed Avalanche Current (Note 3)		I _{AS}	20	А	
Total Power Dissipation @ T _C = 25°C		P _{DTOT}	46	W	
Operating Junction and Storage Temperature Range		T_J,T_STG	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R _{eJC}	2.7	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62	°C/W	

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air



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PARAMETER	CONDITIONS			ТҮР	MAX	UNIT
Static (Note 4)				•		•
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 uA$	V _{GS(TH)}	1.2	1.7	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
	$V_{DS} = 60V, V_{GS} = 0V$ $V_{DS} = 48V, V_{GS} = 0V,$ I_{DSS} $I_{J} = 125^{\circ}C$				1	
Zero Gate Voltage Drain Current					10	μA
	$V_{GS} = 10V, I_D = 20A$			15	17	
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_{D} = 10A$	R _{DS(ON)}		17.5	20	mΩ
Dynamic (Note 5)		-			•	
Total Gate Charge		Qg		15		nC
Gate-Source Charge	$V_{DS} = 30V, I_D = 10A,$	Q _{gs}		5.5		
Gate-Drain Charge	$V_{GS} = 4.5V$	Q _{gd}		5		
Input Capacitance		C _{iss}		900		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		130		pF
Reverse Transfer Capacitance		C _{rss}		90		1
Gate Resistance	F = 1MHz, open drain	R _g		2.2		Ω
Switching ^(Note 6)	·					
Turn-On Delay Time		t _{d(on)}		8.6		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 15V,$	t _r		24.2		
Turn-Off Delay Time	$R_{G} = 6\Omega, I_{D} = 1A$	t _{d(off)}		32.3		ns
Turn-Off Fall Time	-	t _f		7.9		
Source-Drain Diode (Note 4)						•
Diode Forward Voltage	V _{GS} =0V, I _S =10A	V _{SD}			1	V
Reverse Recovery Time	$V_{GS} = 0V, I_{S} = 10A$	t _{rr}	-	18		ns
Reverse Recovery Charge	dI _F /dt = 100A/µs	Q _{rr}		10		nC

Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. L = 0.1mH, I_{AS} = 20A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 ^{o}C

4. Pulse test: PW \leq 300µs, duty cycle \leq 2%

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM170N06CP ROG	TO-252(D-PAK)	2,500pcs / 13" Reel
TSM170N06CH C5G	TO-251(I-PAK)	75pcs / Tube
TSM170N06CH X0G	TO-251S(I-PAK SL)	75pcs / Tube

Note:

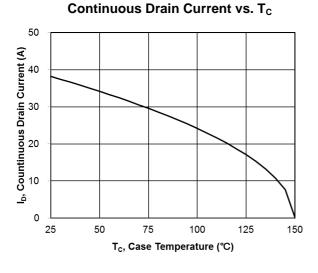
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

2. Halogen-free according to IEC 61249-2-21 definition

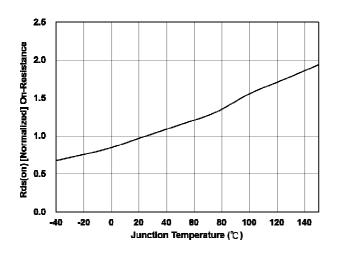


CHARACTERISTICS CURVES

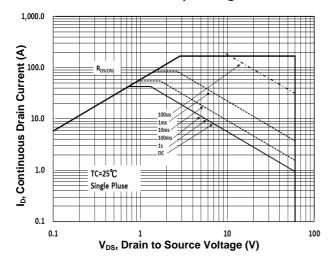
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$

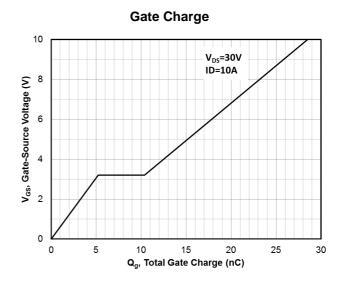


On-Resistance vs. Junction Temperature

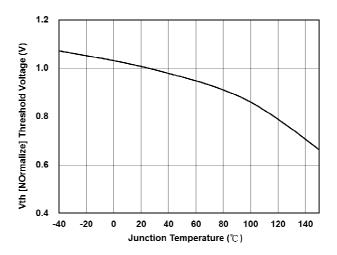


Maximum Safe Operating Area

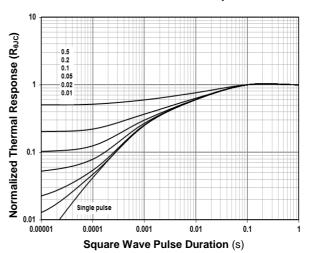




Threshold Voltage vs. Junction Temperature



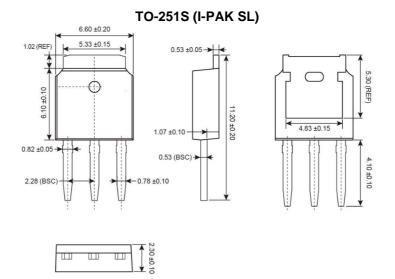
Normalized Thermal Transient Impedance Curve







PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



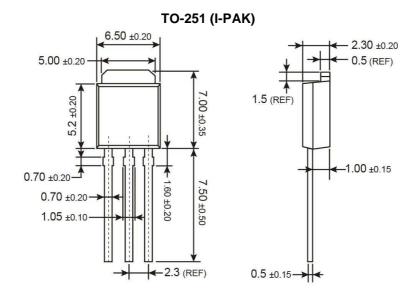
MARKING DIAGRAM



- Y = Year Code
- **M** = Month Code for Halogen Free Product



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM

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Y = Year Code

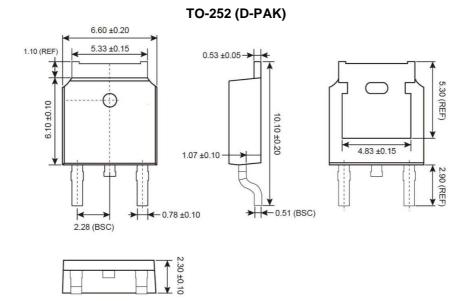
M = Month Code for Halogen Free Product

O =Jan	P =Feb	Q =Mar	R =Apr
S =May	T =Jun	U =Jul	V =Aug
W =Sep	X =Oct	Y =Nov	Z =Dec

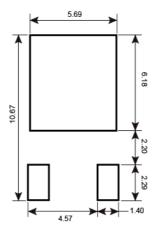
L = Lot Code (1~9, A~Z)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



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	O =Jan	Ρ	=Feb	Q	=Mar	R	=Apr
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